

Abstract Submitted
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Computational Discovery of a Novel Semiconductor: A Vacancy-Ordered $\text{Fe}_{1.5}\text{TiSb}$ Heusler Phase VINAY ISHWAR HEGDE, Northwestern University, NARIMAN NAGHIBOLASHRAFI, SAHAR KESHAVARZ, KAMARAM MUNIRA, WILLIAM BUTLER, PATRICK LECLAIR, The University of Alabama, CHRIS WOLVERTON, Northwestern University — Many full- and half-Heusler phase compounds are half-metallic ferromagnets, and are attractive for spintronic applications due to their relatively high Curie temperatures. However, while it is known that defects such as vacancies (on the X site of an X_2YZ Heusler phase) can lead to a loss of half-metallic character, their effect on the stability and order of these compounds has not been adequately explored. To address this shortcoming, we perform a binary cluster expansion (CE) of Fe and vacancies on the Fe sublattice of the $\text{Fe}_x\text{Vac}_{2-x}\text{TiSb}$ Heusler compound. From our CE, we computationally predict the stability of a novel semiconductor phase with an interesting new structure type: $R\bar{3}m$ spacegroup with composition $\text{Fe}_{1.5}\text{TiSb}$, i.e., between the full- and half-Heusler compositions. By comparing the electronic structure of all the competing structures at $x = 1.5$, we find that the gap opened in the minority-spin channel due to vacancies strongly correlates with the stability of the structure. We study the effect of vacancies on the structural order in $\text{Fe}_{1.5}\text{TiSb}$ by generating special quasirandom structures (SQSs) as approximations to the true disordered state, and find that the material undergoes an order-disorder transition at elevated temperatures of ~ 1450 K.

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